

N-channel TrenchMOS logic level FET Rev. 2 — 7 February 2011

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources

Motors, lamps and solenoids

Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

Table 1

- 12 V loads
- Automotive and general purpose power switching

Quick reference data

1.4 Quick reference data

Table 1.	QUICK reference	uata					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	75	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	300	W
Static cha	aracteristics						
R _{DSon} drain-source on-state resistance	V _{GS} = 4.3 V; I _D = 25 A; T _j = 25 °C		-	3.7	5.9	mΩ	
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C		-	2.9	4	mΩ
		$\label{eq:GS} \begin{array}{l} V_{GS} = 5 \; V; \; I_{D} = 25 \; A; \\ T_{j} = 25 \; ^{\circ}C; \; see \; \underline{Figure \; 11}; \\ see \; \underline{Figure \; 12} \end{array}$		-	3.5	4.4	mΩ



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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 75 \text{ A}; V_{sup} \leq 40 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 5 V; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{unclamped} \end{split}$	-	-	1.6	J
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 5 V; I_D = 25 A;$ $V_{DS} = 32 V; T_j = 25 °C;$ see Figure 13	-	56	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9604-40A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	40	V
V _{GS}	gate-source voltage			-15	15	V
I _D	drain current	T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	<u>[1]</u>	-	75	А
		$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } Figure 1;$	<u>[1]</u>	-	75	А
		see Figure 3		-	198	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>		-	794	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	300	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
Is	source current	T _{mb} = 25 °C	[3]	-	198	А
		[1]		-	75	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	794	А
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le 40$ V; $R_{GS} = 50$ Ω; $V_{GS} = 5$ V; $T_{j(init)} = 25$ °C; unclamped		-	1.6	J

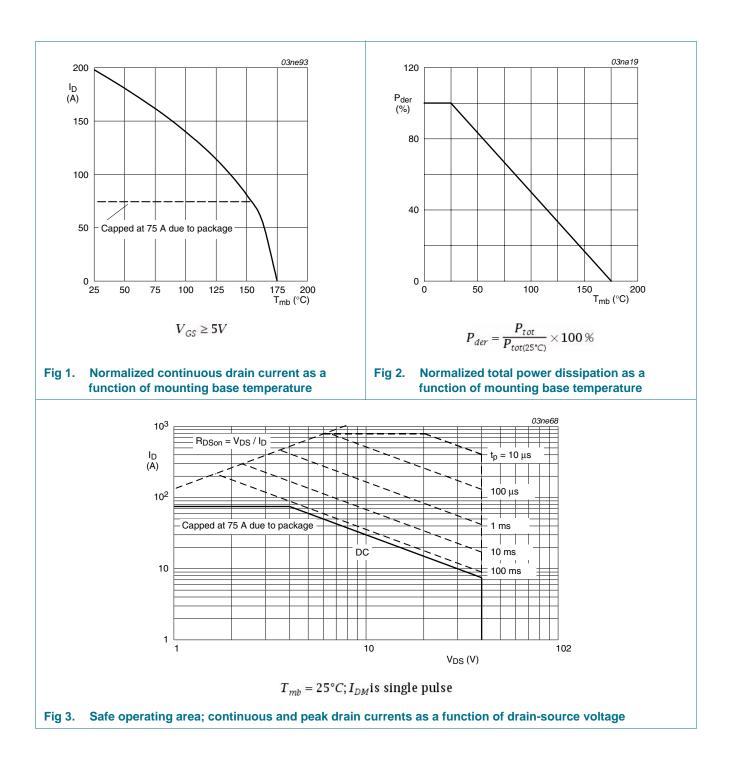
[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.

[3] Current is limited by power dissipation chip rating

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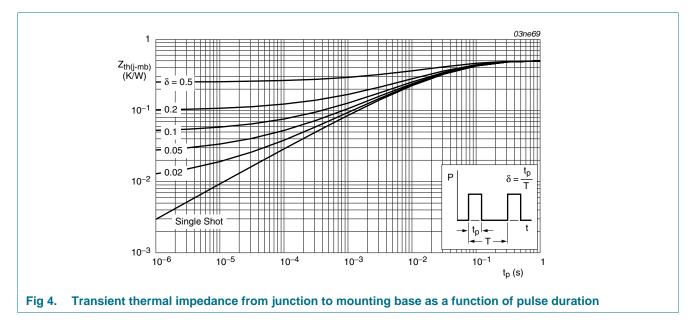
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed circuit board; minimum footprint	-	50	-	K/W



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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 10</u>	1	1.5	2	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 10</u>	0.5	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.3 V; I _D = 25 A; T _j = 25 °C	-	3.7	5.9	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	2.9	4	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	8.3	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	3.5	4.4	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$	-	128	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$	-	13	-	nC
Q _{GD}	gate-drain charge		-	56	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	6200	8260	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	1040	1250	pF
C _{rss}	reverse transfer capacitance		-	680	940	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 5 V;	-	62	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	309	-	ns
t _{d(off)}	turn-off delay time		-	365	-	ns
t _f	fall time		-	306	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH

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ble 6.	Characteristics continued	Conditions			T	M	11!!
/mbol	Parameter	Conditions		Min	Тур	Max	Unit
	rain diode				0.05	4.0	N
SD	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}$ see <u>Figure 15</u>	·	-	0.85	1.2	V
	reverse recovery time	$I_{\rm S} = 20 \text{ A}; \text{ d}I_{\rm S}/\text{d}t = -1$		-	260	-	ns
	recovered charge	V _{GS} = -10 V; V _{DS} = 3	$30 \text{ V}; \text{ I}_{\text{j}} = 25 \text{ °C}$	-	531	-	nC
				9 $f_j = 25^{\circ}C; I_D =$ the on-state re	= 25A	03nd94	Inction
	function of drain-source volt			rce voltage;			
10 ⁻³	min <u>/</u> / / / / / / / / / / / / / /		60 40				
10 ⁻⁵		3		40	60	80 I _D (A)	
10 ⁻⁶	0 1 2	V _{GS} (V)				.0 (, ,)	
	0 1 2 $T_j = 25 ^{\circ}C; V_{DS} = V_0$	V _{GS} (V)	T_{j}	$= 25^{\circ}C; V_{DS}$			

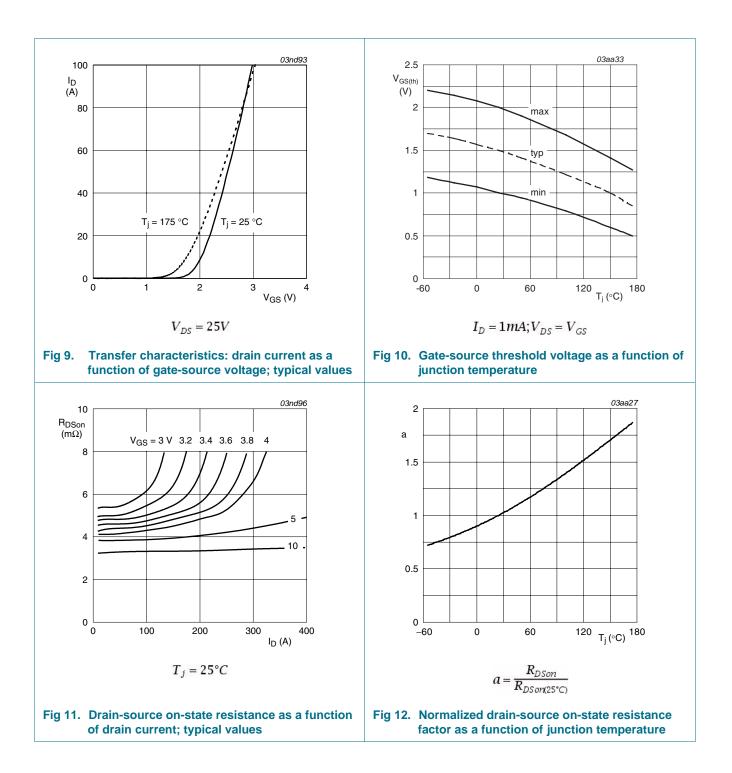
Table 6. Characteristics ...continued

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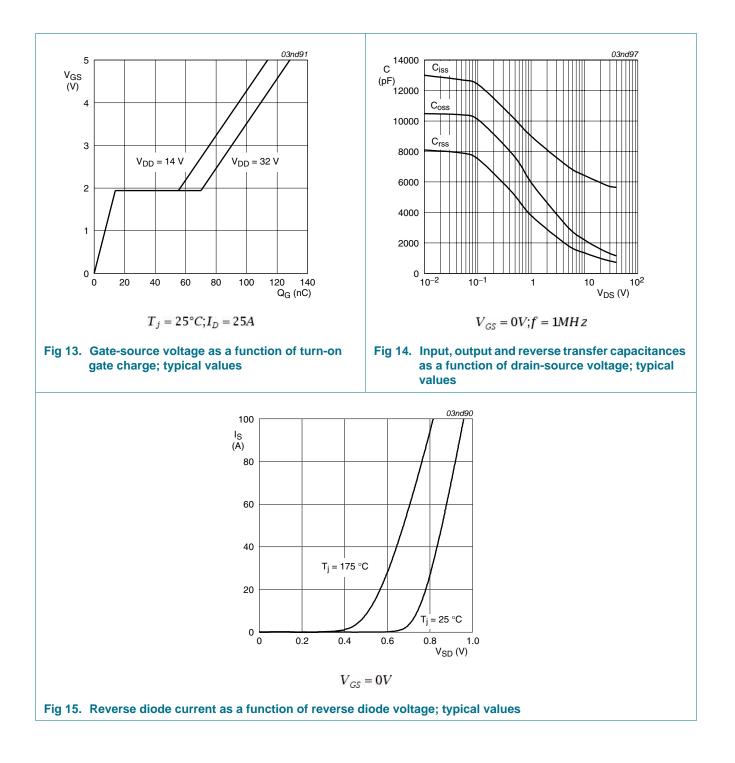
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7. Package outline

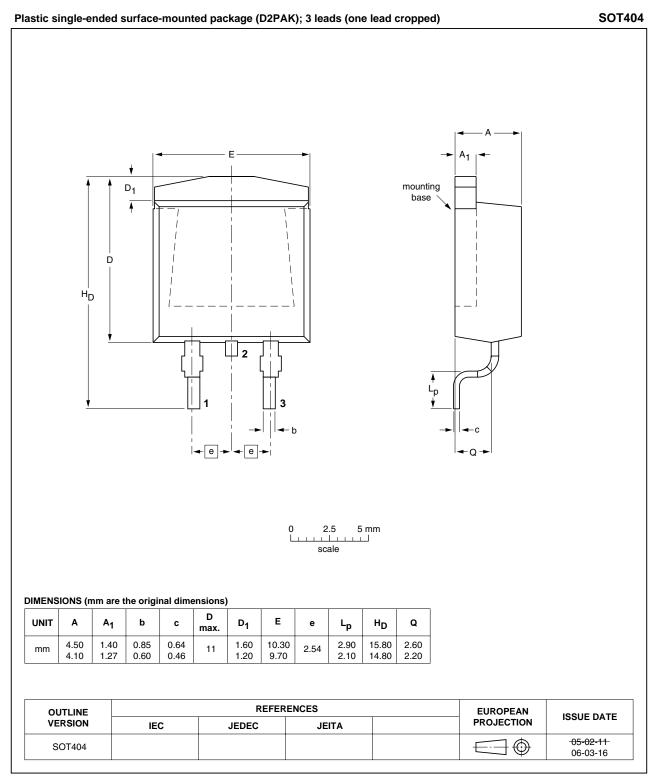


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7.	Revision history					
Document	ID	Release date	Data sheet status	Change notice	Supersedes	
BUK9504-4	40A v.2	20110207	Product data sheet	-	BUK95_96_9E04_40A-01	
Modifications:		 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
		 Legal texts 	have been adapted to the	new company nam	e where appropriate.	
		 Type number 	er BUK9504-40A separate	d from data sheet E	3UK95_96_9E04_40A-01.	
BUK95_96	_9E04_40A-01	20011024	Product specification	-	-	

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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